UNIKC
Semiconductor

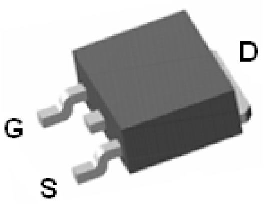
RoHS
Compliant

P2806BD

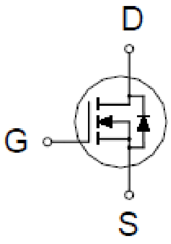
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
60V	28mΩ @V_{GS} = 10V	30A



TO-252



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25 °C	I_D	30	A
	T_C = 100 °C		19	
Pulsed Drain Current[1]		I_{DM}	100	
Avalanche Current		I_{AS}	30	
Avalanche Energy	L = 0.1mH	E_{AS}	43	mJ
Power Dissipation	T_C = 25 °C	P_D	50	W
	T_C = 100 °C		20	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		2.5	°C / W
Junction-to-Ambient	$R_{\theta JA}$		40	

[1] Pulse width limited by maximum junction temperature.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	1.5	3.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±250	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 48V, V_{GS} = 0V			1	μA
		V_{DS} = 40V, V_{GS} = 0V , T_J = 125 °C			10	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 10V, V_{GS} = 10V	100			A
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 12A		28	38	mΩ
		V_{GS} = 10V, I_D = 20A		22.3	28	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 20A		25		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		1500		pF
Output Capacitance	C_{oss}			168		
Reverse Transfer Capacitance	C_{rss}			106		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		1.3		Ω
Total Gate Charge[2]	Q_g	V_{DS} = 30V, V_{GS} = 10V, I_D = 20A		27.4		nC
Gate-Source Charge[2]	Q_{gs}			6.1		
Gate-Drain Charge[2]	Q_{gd}			5.8		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 30V, $I_D \cong$ 20A, V_{GS} = 10V, R_{GEN} = 6Ω		8		nS
Rise Time[2]	t_r			6		
Turn-Off Delay Time[2]	$t_{d(off)}$			29		
Fall Time[2]	t_f			6		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				30	A
Forward Voltage[1]	V_{SD}	I_F = 20A, V_{GS} = 0V			1.3	V
Reverse Recovery Time	t_{rr}	IF = 20A, dI_F/dt = 100A / μS		41		nS
Reverse Recovery Charge	Q_{rr}			46		nC

[1] Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2] Independent of operating temperature.

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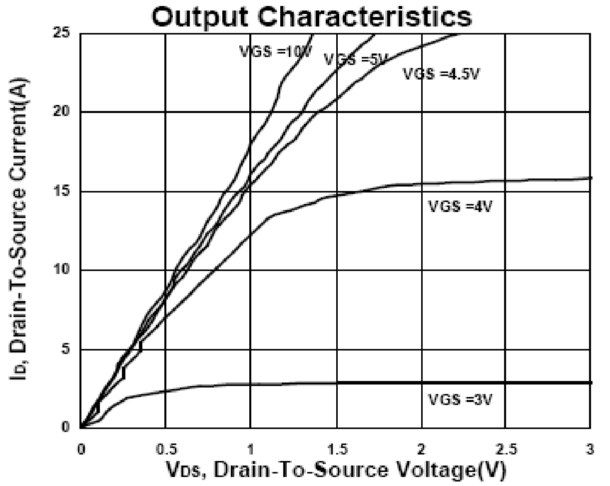
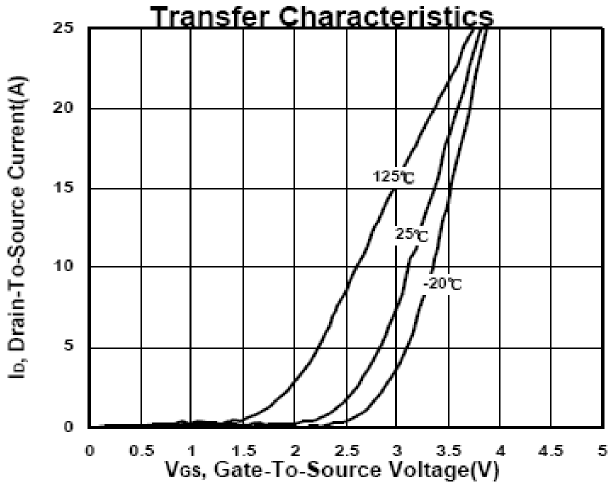
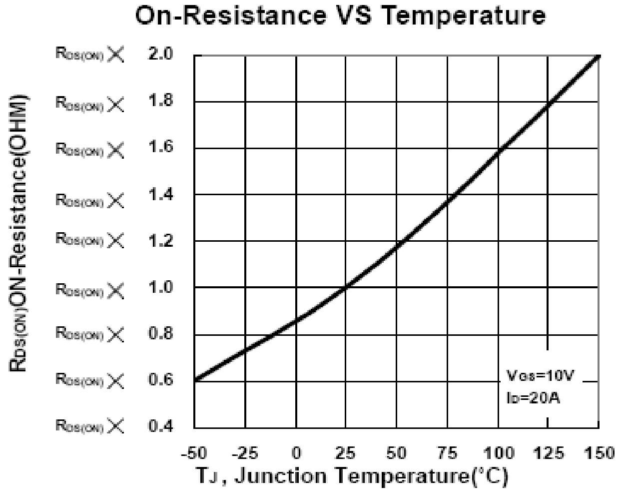
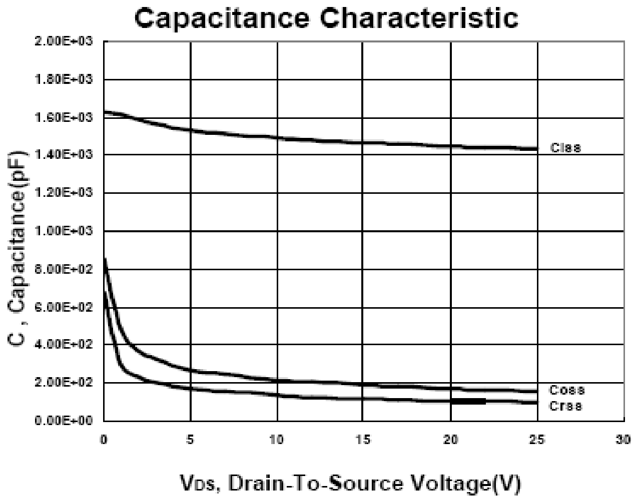
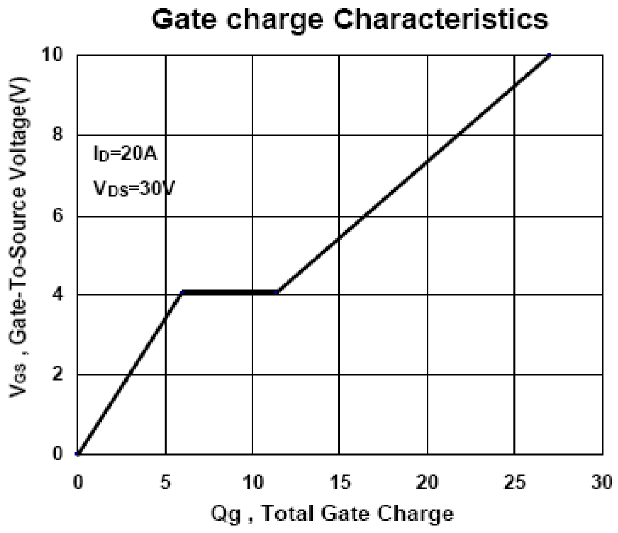
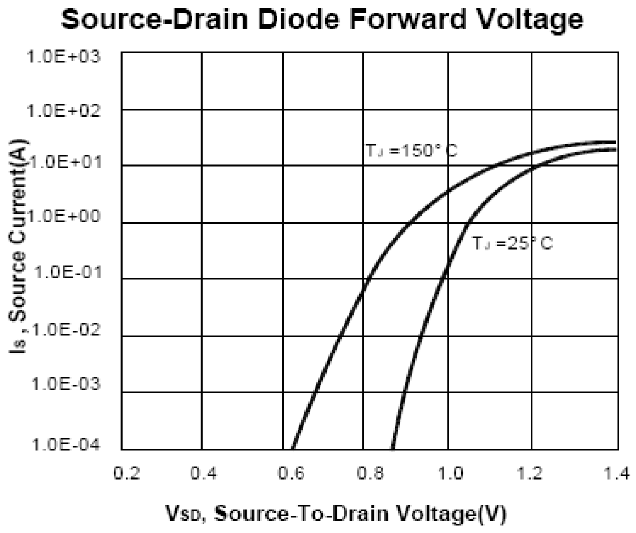

Output Characteristics


Transfer Characteristics


On-Resistance VS Temperature


Capacitance Characteristic


Gate charge Characteristics


Source-Drain Diode Forward Voltage

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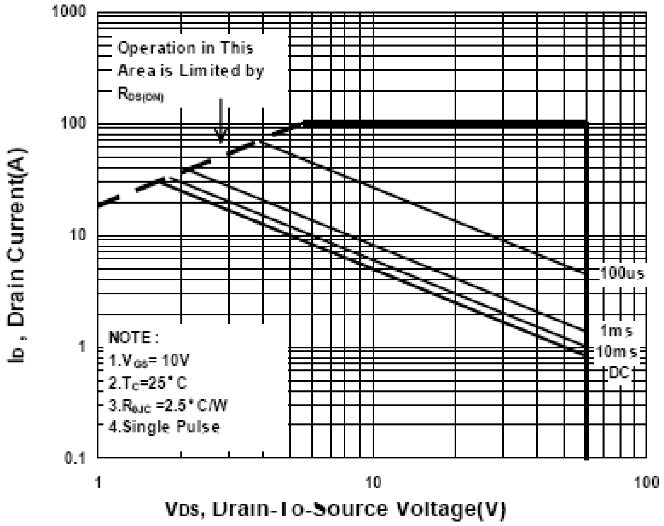
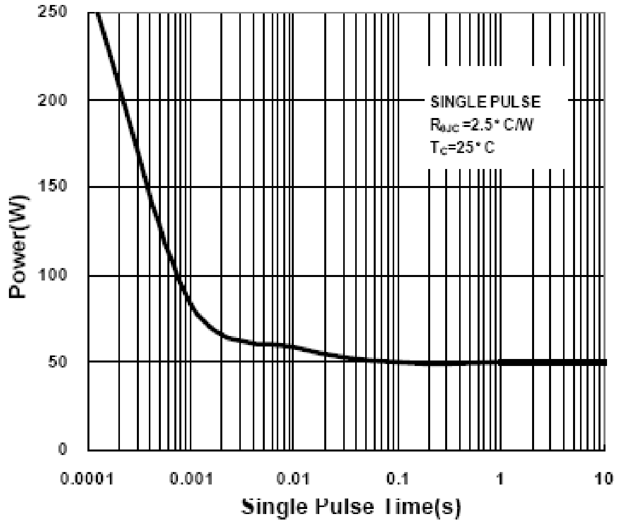
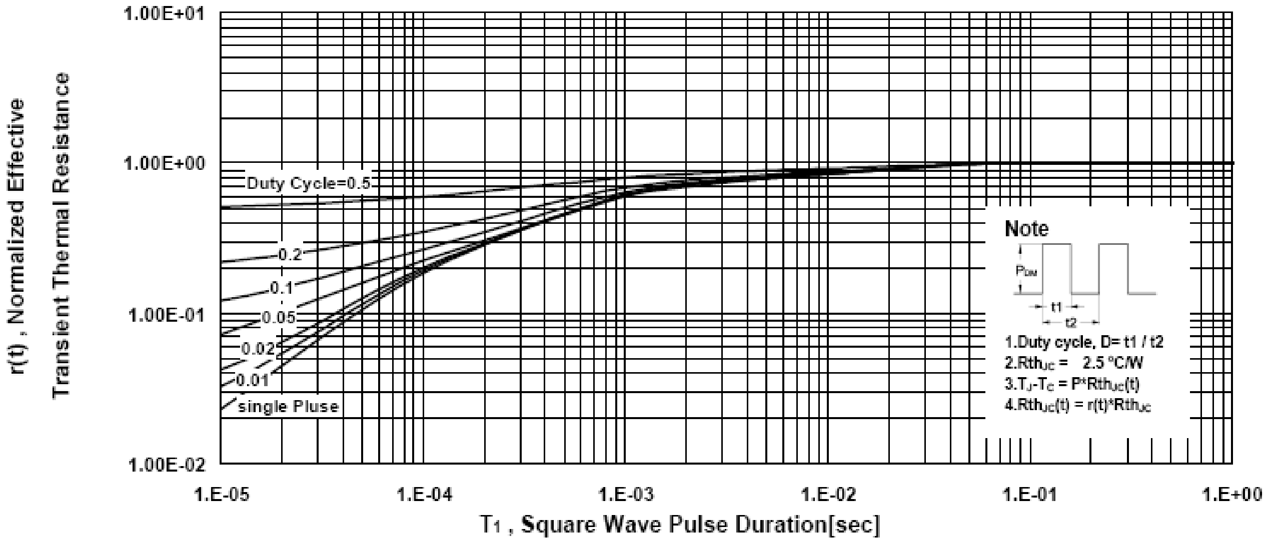
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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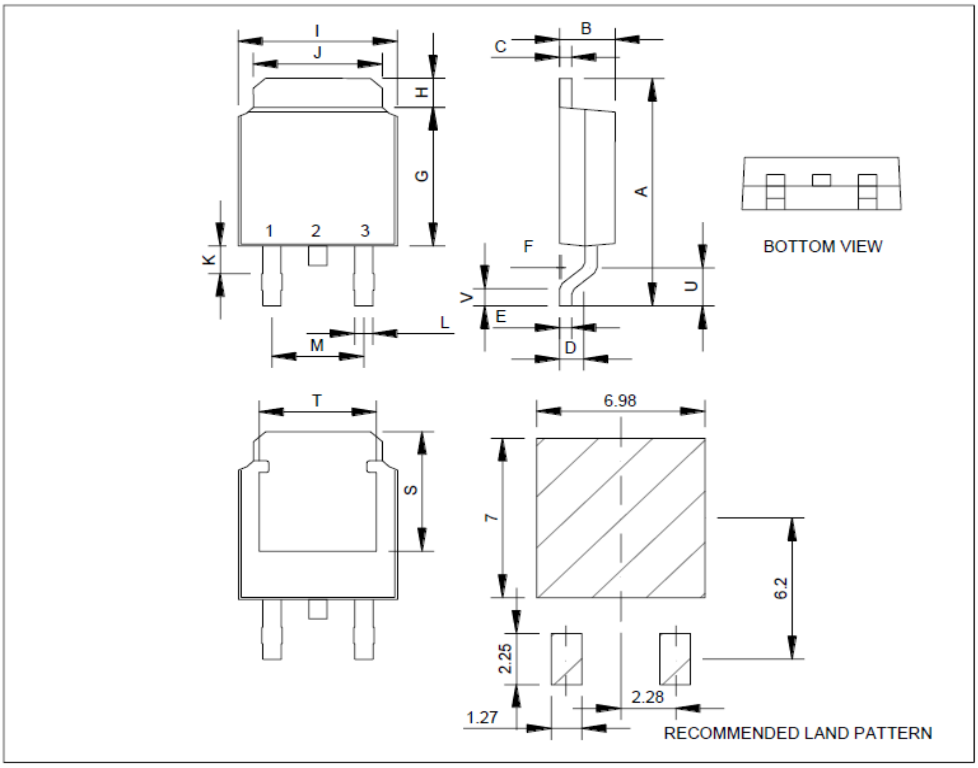
Package Dimension

TO-252 (DPAK) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	8.9	10	10.41	J	4.8		5.64
B	2.1	2.2	2.4	K	0.15		1.1
C	0.4	0.5	0.61	L	0.4	0.76	0.89
D	0.82	1.2	1.5	M	4.2	4.58	5
E	0.4	0.5	0.61	S	4.9	5.1	5.3
F	0		0.2	T	4.6	4.75	5.44
G	5.3	6.1	6.3	U	1.4		1.78
H	0.9		1.7	V	0.55	1.25	1.7
I	6.3	6.5	6.8				



*因为各家封装模具不同而外观略有所差异，不影响电性及Layout。

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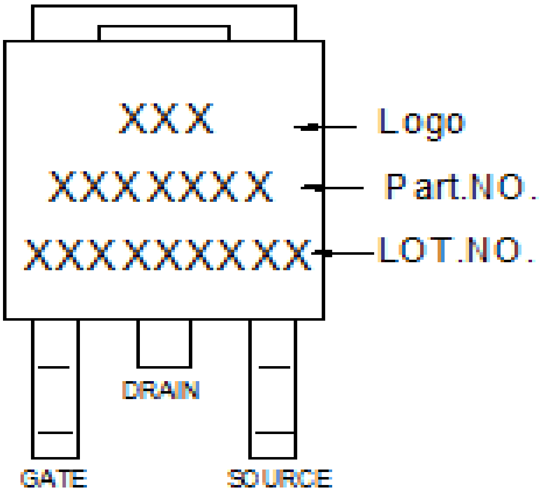
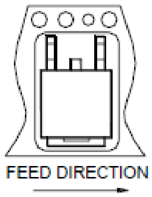
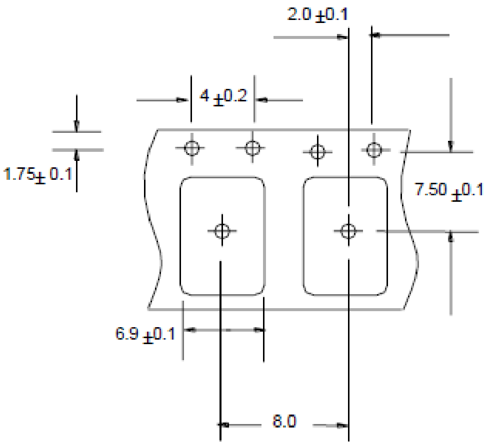
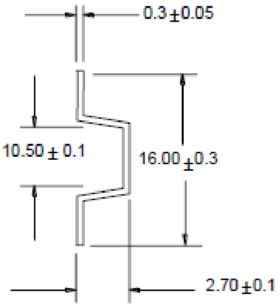
A. Marking Information

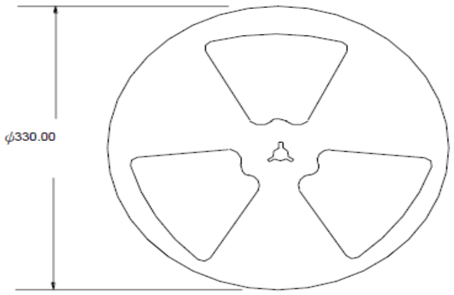


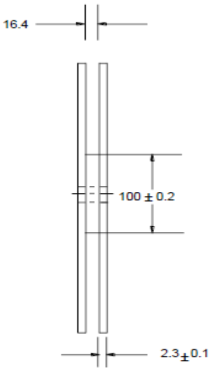
B. Tape&Reel Information:2500pcs/Reel





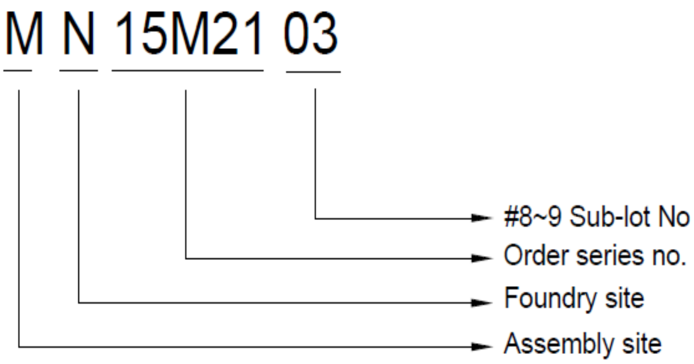




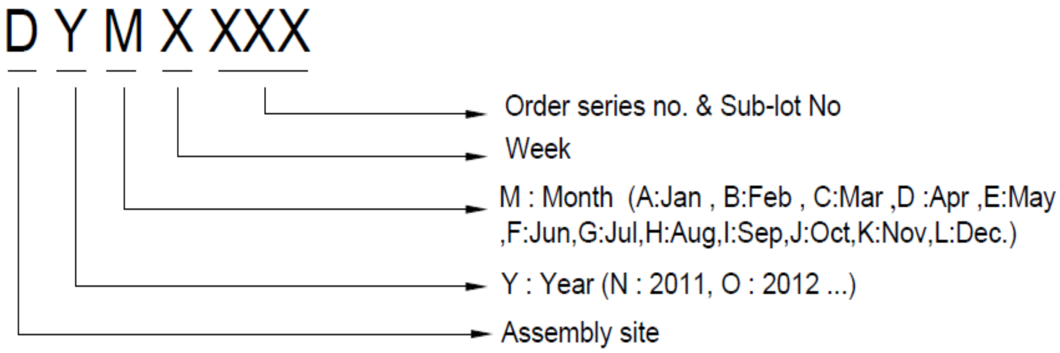


C. Lot.No. & Date Code rule

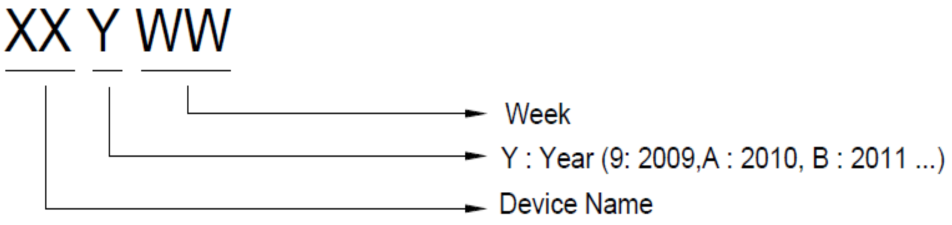
1.LOT.NO.



2.Date Code



3.Date Code (for Small package)



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D.Label rule

标签内容(Label content)

1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial （或可区分英文”O”和数字”0”，”G和”Q”的字型即可）
3	Great Power	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	Pb Free label	 Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
11	Halogen Free label	 Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
12	Scan info	Device / Lot / D/C / QTY , Insert “ / “ between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least